

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D Max $T_C = +25^\circ C$
60V	25m Ω @ $V_{GS} = 10V$	32A
	40m Ω @ $V_{GS} = 4.5V$	25A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

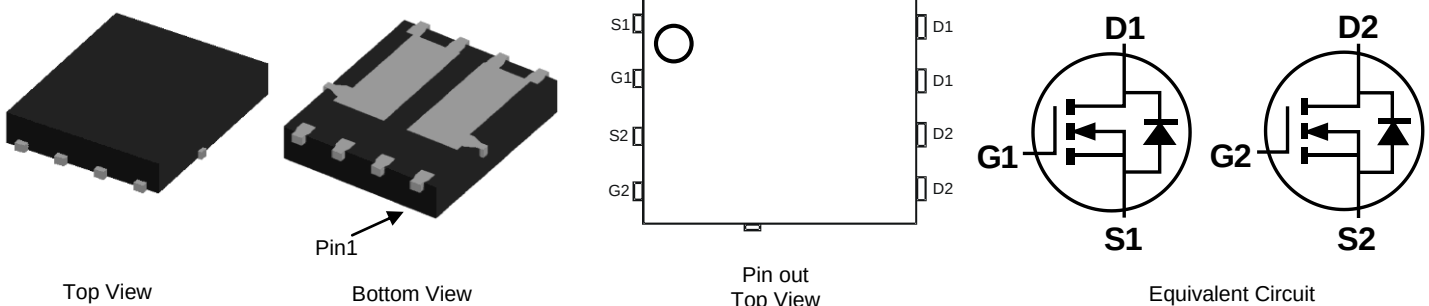
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Rated to $+175^\circ C$ – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Complaint Part is Available Under Separate Datasheet ([DMNH6021SPDQ](#))**

Mechanical Data

- Case: PowerDI[®]5060-8 (Type C)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

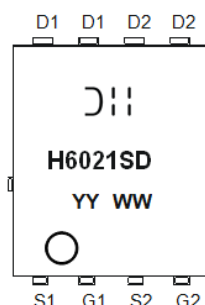


Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH6021SPD-13	PowerDI5060-8 (Type C)	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 3. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



 = Manufacturer's Marking
 H6021SD = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 16 = 2016)
 WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	T _A = +25°C 8.2	A
		T _A = +70°C 6.5	
Continuous Drain Current (Note 7) V _{GS} = 10V	I _D	T _C = +25°C 32	A
		T _C = +100°C 22	
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I _{DM}	80	A
Maximum Continuous Body Diode Forward Current (Note 7)	I _S	32	A
Avalanche Current, L = 0.1mH (Note 8)	I _{AS}	35	A
Avalanche Energy, L = 0.1mH (Note 8)	E _{AS}	64	mJ

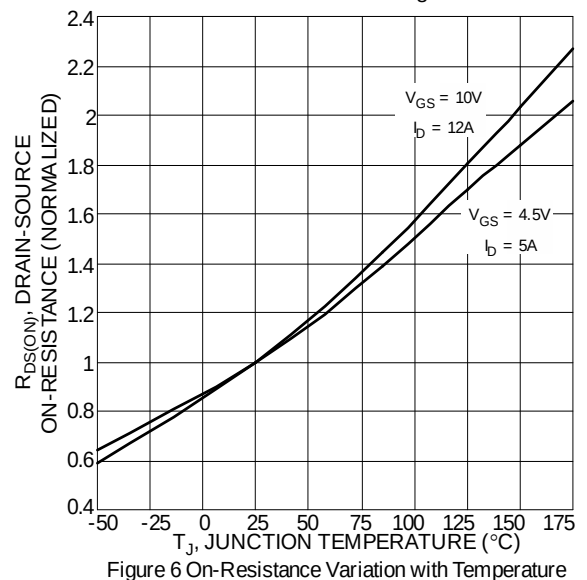
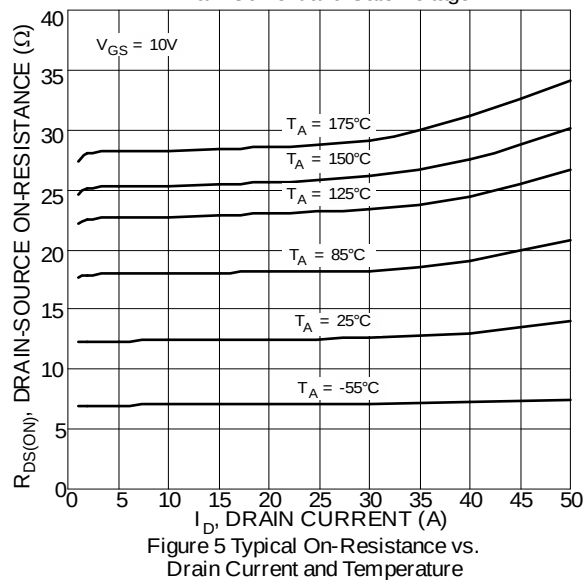
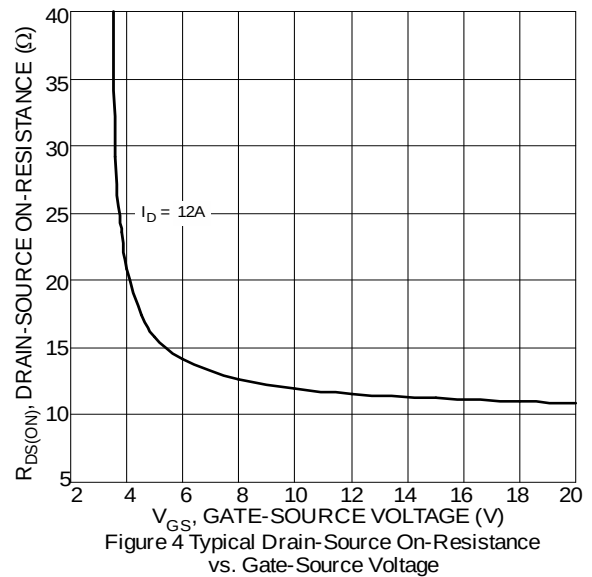
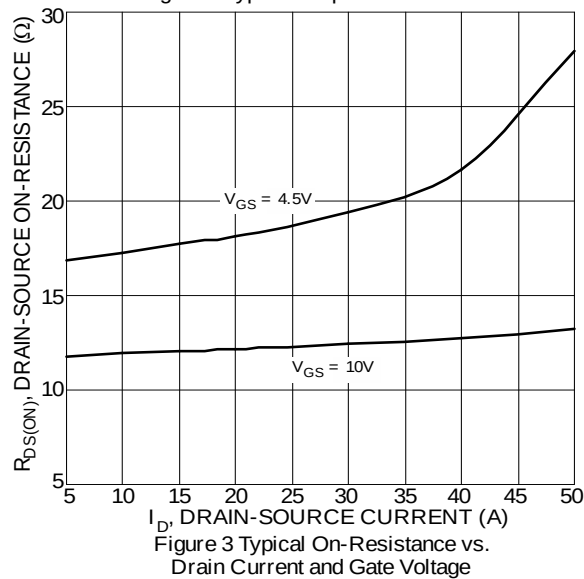
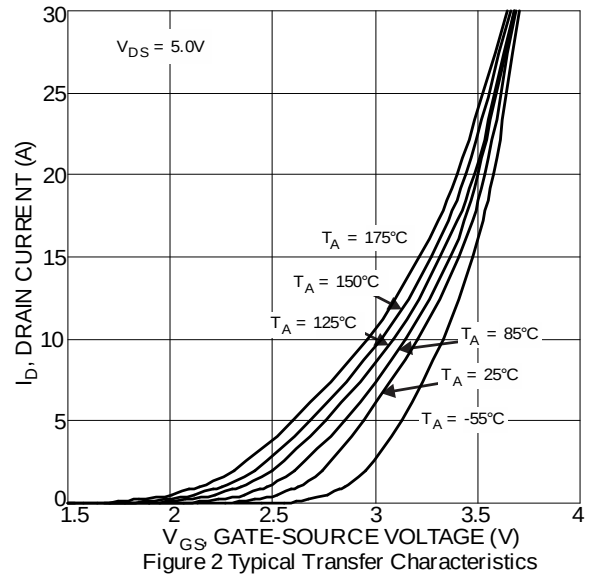
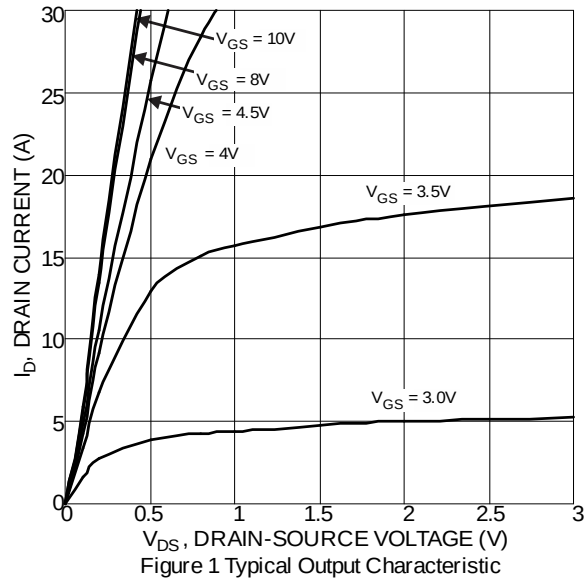
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

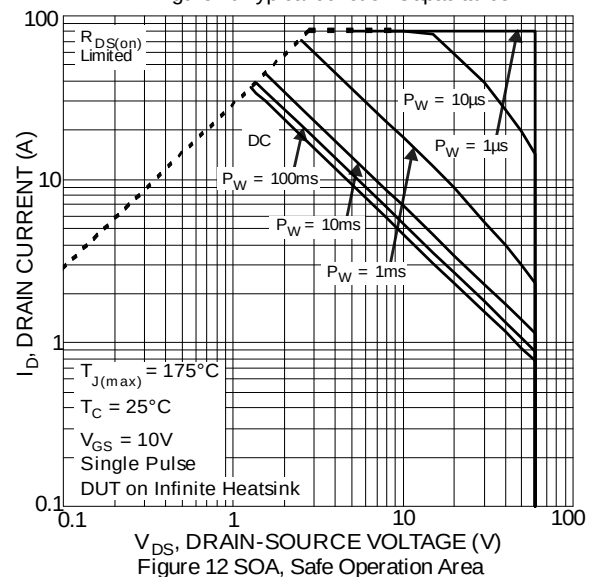
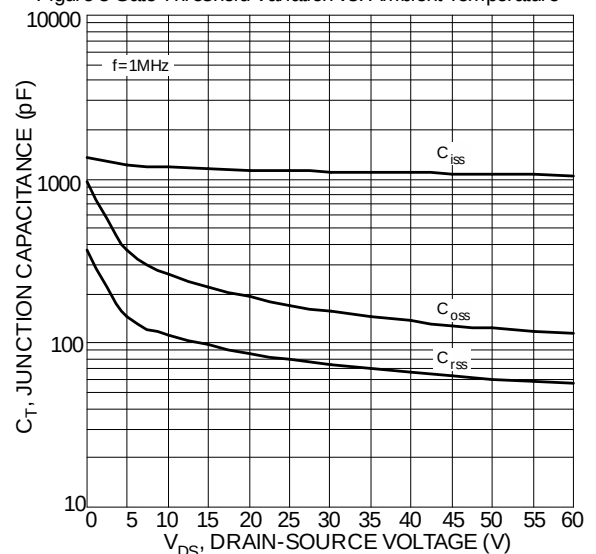
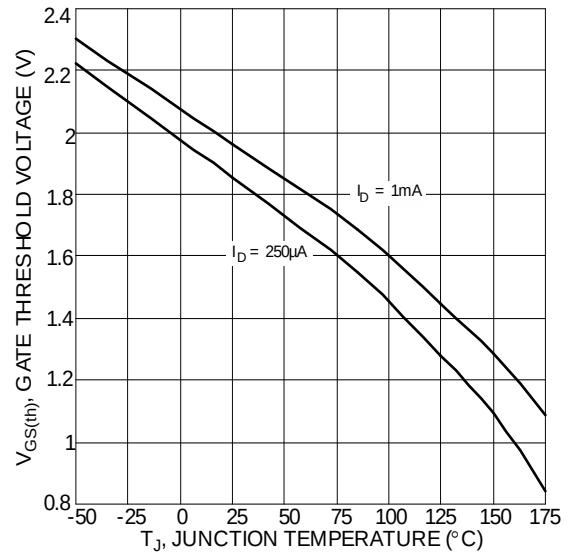
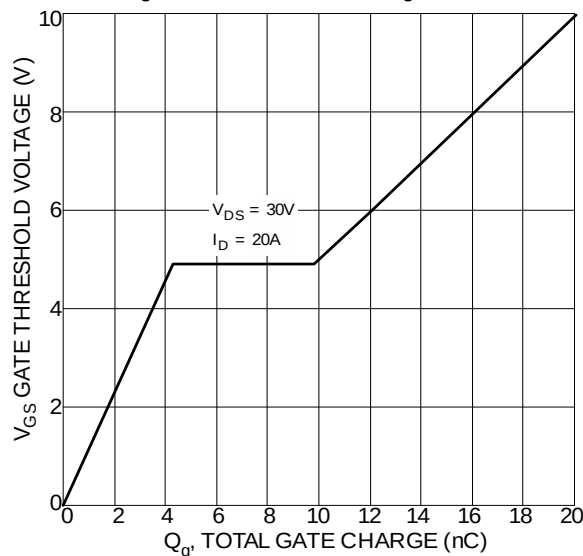
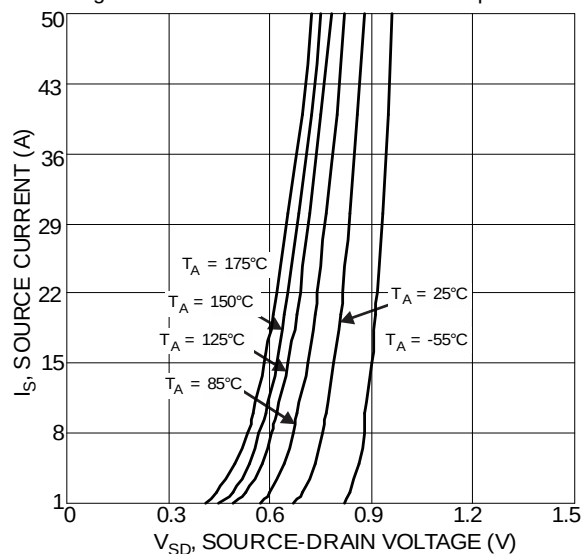
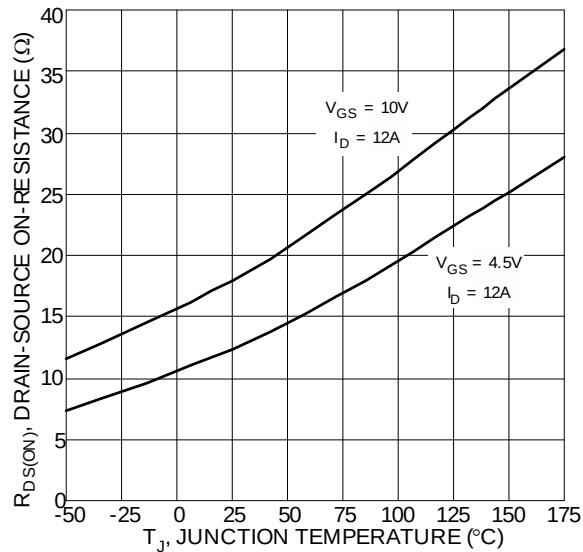
Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	Steady State 99	°C/W
		t<10s 53	
Total Power Dissipation (Note 6)	P _D	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	Steady State 54	°C/W
		t<10s 27	
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	2.2	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

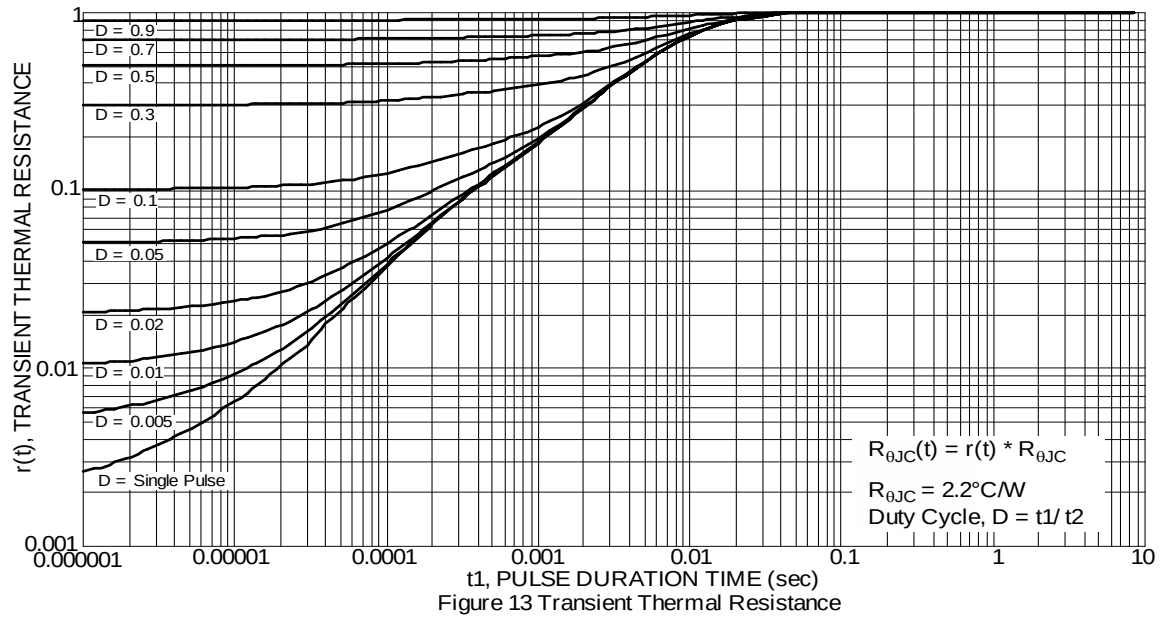
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	µA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	15	25	mΩ	V _{GS} = 10V, I _D = 15A
		—	21	40		V _{GS} = 4.5V, I _D = 12A
Diode Forward Voltage	V _{SD}	—	0.75	1.2	V	V _{GS} = 0V, I _S = 2.6A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{ISS}	—	1,143	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{OSS}	—	168	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	69	—	pF	
Gate Resistance	R _G	—	2.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _G	—	20.1	—	nC	V _{DS} = 30V, I _D = 20A,
Total Gate Charge (V _{GS} = 6V)	Q _G	—	12	—	nC	
Gate-Source Charge	Q _{GS}	—	4.3	—	nC	
Gate-Drain Charge	Q _{GD}	—	5.5	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	4.4	—	ns	V _{DD} = 30V, V _{GS} = 10V, R _G = 4.7Ω, I _D = 20A
Turn-On Rise Time	t _R	—	6.0	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	14.2	—	ns	
Turn-Off Fall Time	t _F	—	5.4	—	ns	IF=20A, di/dt=100A/µs
Body Diode Reverse Recovery Time	t _{RR}	—	21.2	—	ns	
Body Diode Reverse Recovery Charge	Q _{RR}	—	15.2	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = 25°C
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



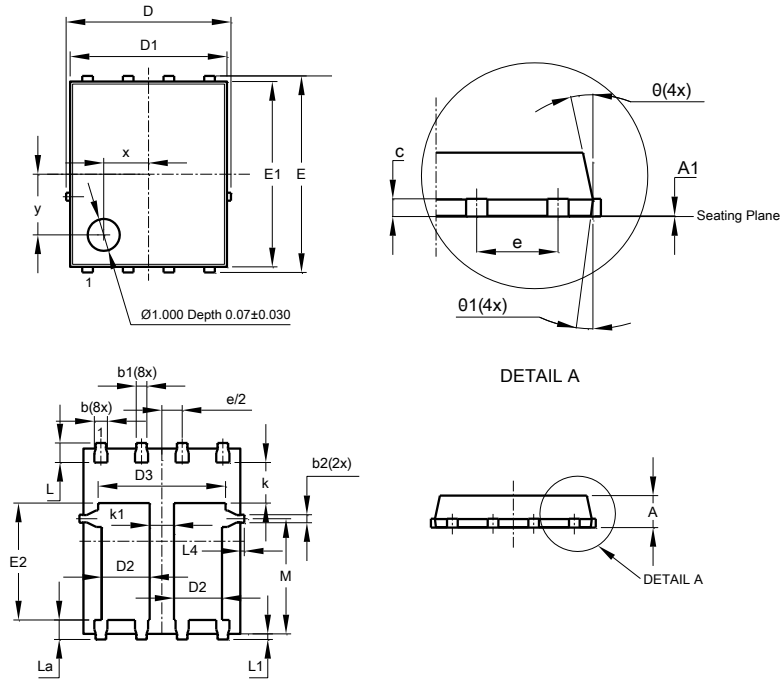




Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type C)

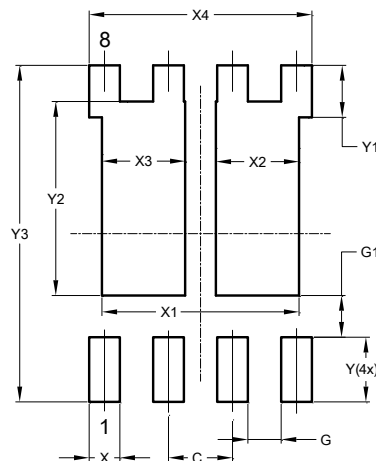


PowerDI5060-8 (Type C)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	1.40	1.60	1.50
D3	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.76	3.66
e	1.27BSC		
k	-	-	1.27
k1	0.56	-	-
L	0.51	0.71	0.61
La	0.51	0.71	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
θ	10°	12°	11°
Ø1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type C)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	1.650
X3	1.650
X4	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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